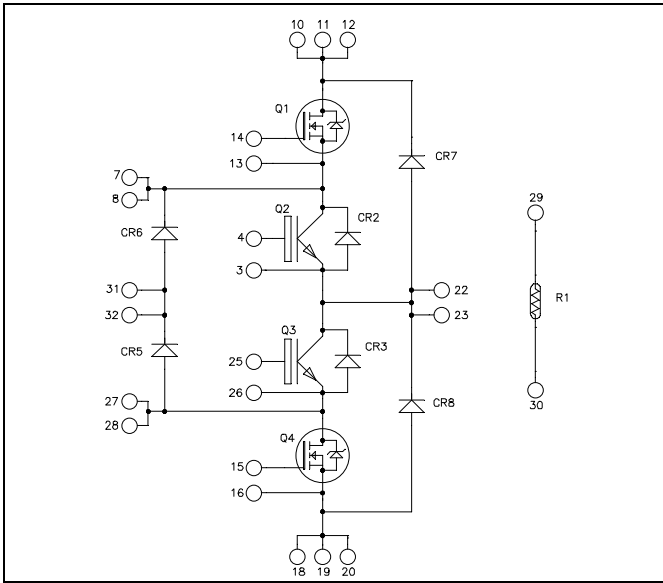


*Three level inverter
CoolMOS & Trench + Field Stop IGBT
Power Module*

Trench & Field Stop IGBT Q2, Q3:
 $V_{CES} = 600V$; $I_C = 75A$ @ $T_c = 80^\circ C$

CoolMOS™ Q1, Q4:
 $V_{DSS} = 600V$; $I_D = 38A$ @ $T_c = 80^\circ C$

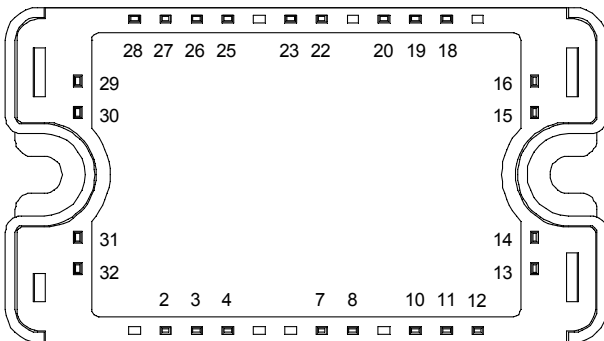


Application

- Solar converter
- Uninterruptible Power Supplies

Features

- **Q2, Q3 Trench + Field Stop IGBT Technology**
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 20 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - RBSOA and SCSOA rated
- **Q1, Q4 CoolMOS™**
 - Ultra low R_{DSon}
 - Low Miller capacitance
 - Ultra low gate charge
 - Avalanche energy rated
 - Very rugged
- Kelvin emitter for easy drive
- Very low stray inductance
- High level of integration
- Internal thermistor for temperature monitoring



All multiple inputs and outputs must be shorted together
 Example: 10/11/12 ; 7/8 ...

Benefits

- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of V_{CEsat}
- Low profile
- RoHS Compliant

All ratings @ $T_j = 25^\circ C$ unless otherwise specified

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.
 See application note APT0502 on www.microsemi.com

Q1 & Q4 Absolute maximum ratings

<i>Symbol</i>	<i>Parameter</i>	<i>Max ratings</i>	<i>Unit</i>
V _{DSS}	Drain - Source Breakdown Voltage	600	V
I _D	Continuous Drain Current	T _c = 25°C	49
		T _c = 80°C	38
I _{DM}	Pulsed Drain current	130	A
V _{GS}	Gate - Source Voltage	±20	V
R _{DS(on)}	Drain - Source ON Resistance	45	mΩ
P _D	Maximum Power Dissipation	T _c = 25°C	250
I _{AR}	Avalanche current (repetitive and non repetitive)	15	A
E _{AR}	Repetitive Avalanche Energy	3	mJ
E _{AS}	Single Pulse Avalanche Energy	1900	

Q1 & Q4 Electrical Characteristics

<i>Symbol</i>	<i>Characteristic</i>	<i>Test Conditions</i>	<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
I _{DSS}	Zero Gate Voltage Drain Current	V _{GS} = 0V, V _{DS} = 600V T _j = 25°C			250	μA
		V _{GS} = 0V, V _{DS} = 600V T _j = 125°C			500	
R _{DS(on)}	Drain – Source on Resistance	V _{GS} = 10V, I _D = 24.5A		40	45	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{GS} = V _{DS} , I _D = 3mA	2.1	3	3.9	V
I _{GSS}	Gate – Source Leakage Current	V _{GS} = ±20 V, V _{DS} = 0V			100	nA

Q1 & Q4 Dynamic Characteristics

<i>Symbol</i>	<i>Characteristic</i>	<i>Test Conditions</i>	<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
C _{iss}	Input Capacitance	V _{GS} = 0V ; V _{DS} = 25V f = 1MHz		7.2		nF
C _{oss}	Output Capacitance			8.5		
Q _g	Total gate Charge	V _{GS} = 10V V _{Bus} = 300V I _D = 49A		150		nC
Q _{gs}	Gate – Source Charge			34		
Q _{gd}	Gate – Drain Charge			51		
T _{d(on)}	Turn-on Delay Time	Inductive Switching (125°C) V _{GS} = 10V V _{Bus} = 400V I _D = 49A R _G = 5Ω		21		ns
T _r	Rise Time			30		
T _{d(off)}	Turn-off Delay Time			100		
T _f	Fall Time			45		
E _{on}	Turn-on Switching Energy	Inductive switching @ 25°C V _{GS} = 10V ; V _{Bus} = 400V I _D = 49A ; R _G = 5Ω		675		μJ
E _{off}	Turn-off Switching Energy			520		
E _{on}	Turn-on Switching Energy	Inductive switching @ 125°C V _{GS} = 10V ; V _{Bus} = 400V I _D = 49A ; R _G = 5Ω		1100		μJ
E _{off}	Turn-off Switching Energy			635		
R _{thJC}	Junction to Case Thermal Resistance				0.5	°C/W

Q2 & Q3 Absolute maximum ratings

<i>Symbol</i>	<i>Parameter</i>		<i>Max ratings</i>	<i>Unit</i>
V _{CES}	Collector - Emitter Breakdown Voltage		600	V
I _C	Continuous Collector Current	T _C = 25°C	100	A
		T _C = 80°C	75	
I _{CM}	Pulsed Collector Current	T _C = 25°C	140	
V _{GE}	Gate - Emitter Voltage		±20	V
P _D	Maximum Power Dissipation	T _C = 25°C	250	W
RBSOA	Reverse Bias Safe Operating Area	T _J = 150°C	150A @ 550V	

Q2 & Q3 Electrical Characteristics

<i>Symbol</i>	<i>Characteristic</i>	<i>Test Conditions</i>	<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
I _{CES}	Zero Gate Voltage Collector Current	V _{GE} = 0V, V _{CE} = 600V			250	μA
V _{CE(sat)}	Collector Emitter Saturation Voltage	V _{GE} = 15V I _C = 75A	T _J = 25°C	1.5	1.9	V
			T _J = 150°C	1.7		
V _{GE(th)}	Gate Threshold Voltage	V _{GE} = V _{CE} , I _C = 600μA	5.0	5.8	6.5	V
I _{GES}	Gate - Emitter Leakage Current	V _{GE} = 20V, V _{CE} = 0V			600	nA

Q2 & Q3 Dynamic Characteristics

<i>Symbol</i>	<i>Characteristic</i>	<i>Test Conditions</i>	<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
C _{ies}	Input Capacitance	V _{GE} = 0V V _{CE} = 25V f = 1MHz		4620		pF
C _{oes}	Output Capacitance			300		
C _{res}	Reverse Transfer Capacitance			140		
Q _G	Gate charge	V _{GE} = ±15V, I _C = 75A V _{CE} = 300V		0.8		μC
T _{d(on)}	Turn-on Delay Time	Inductive Switching (25°C) V _{GE} = ±15V V _{Bus} = 300V I _C = 75A R _G = 4.7Ω		110		ns
T _r	Rise Time			45		
T _{d(off)}	Turn-off Delay Time			200		
T _f	Fall Time			40		
T _{d(on)}	Turn-on Delay Time	Inductive Switching (150°C) V _{GE} = ±15V V _{Bus} = 300V I _C = 75A R _G = 4.7Ω		120		ns
T _r	Rise Time			50		
T _{d(off)}	Turn-off Delay Time			250		
T _f	Fall Time			60		
E _{on}	Turn-on Switching Energy	V _{GE} = ±15V V _{Bus} = 300V I _C = 75A	T _J = 25°C	0.35		mJ
			T _J = 150°C	0.6		
E _{off}	Turn-off Switching Energy	R _G = 4.7Ω	T _J = 25°C	2.2		mJ
			T _J = 150°C	2.6		
I _{sc}	Short Circuit data	V _{GE} ≤ 15V ; V _{Bus} = 360V t _p ≤ 6μs ; T _J = 150°C		380		A
R _{thJC}	Junction to Case Thermal Resistance				0.60	°C/W

CR5 & CR6 diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
V _{RRM}	Maximum Peak Repetitive Reverse Voltage			600			V
I _{RM}	Maximum Reverse Leakage Current	V _R =600V	T _j = 25°C			25	μA
			T _j = 125°C			500	
I _F	DC Forward Current	T _c = 80°C			30		A
V _F	Diode Forward Voltage	I _F = 30A			1.8	2.2	V
		I _F = 60A			2.2		
		I _F = 30A	T _j = 125°C		1.5		
t _{rr}	Reverse Recovery Time	I _F = 30A V _R = 400V di/dt = 200A/μs	T _j = 25°C		25		ns
			T _j = 125°C		160		
Q _{rr}	Reverse Recovery Charge		T _j = 25°C		35		nC
			T _j = 125°C		480		
E _{rr}	Reverse Recovery Energy	I _F = 30A V _R = 400V di/dt = 1000A/μs	T _j = 125°C		0.6		mJ
R _{thJC}	Junction to Case Thermal Resistance					1.2	°C/W

CR2, CR3, CR7 & CR8 diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
V _{RRM}	Maximum Peak Repetitive Reverse Voltage			1200			V
I _{RM}	Maximum Reverse Leakage Current	V _R =1200V	T _j = 25°C			100	μA
			T _j = 125°C			500	
I _F	DC Forward Current	T _c = 80°C			30		A
V _F	Diode Forward Voltage	I _F = 30A			2.6	3.1	V
		I _F = 60A			3.2		
		I _F = 30A	T _j = 125°C		1.8		
t _{rr}	Reverse Recovery Time	I _F = 30A V _R = 800V di/dt = 200A/μs	T _j = 25°C		300		ns
			T _j = 125°C		380		
Q _{rr}	Reverse Recovery Charge		T _j = 25°C		360		nC
			T _j = 125°C		1700		
E _{rr}	Reverse Recovery Energy	I _F = 30A V _R = 800V di/dt = 1000A/μs	T _j = 125°C		1.6		mJ
R _{thJC}	Junction to Case Thermal Resistance					1.2	°C/W

Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Typ	Max	Unit
R ₂₅	Resistance @ 25°C		50		kΩ
ΔR ₂₅ /R ₂₅			5		%
B _{25/85}	T ₂₅ = 298.15 K		3952		K
ΔB/B	T _C =100°C		4		%

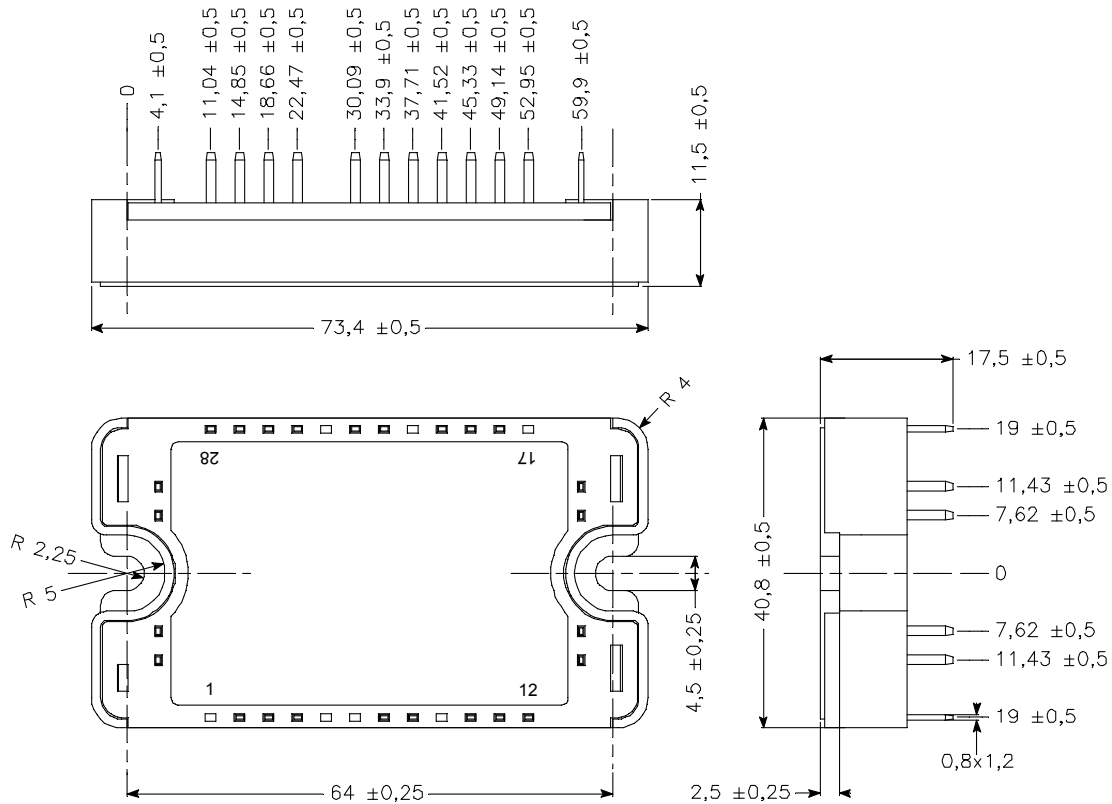
$$R_T = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$

T: Thermistor temperature
 R_T: Thermistor value at T

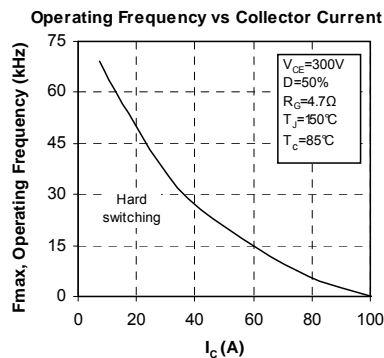
Thermal and package characteristics

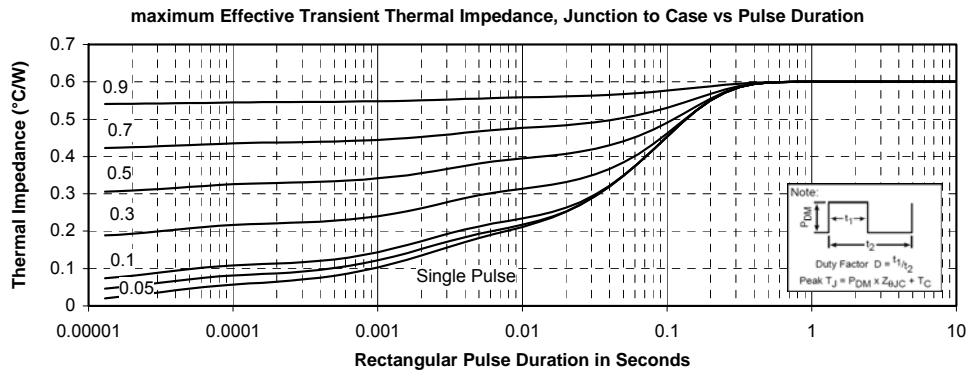
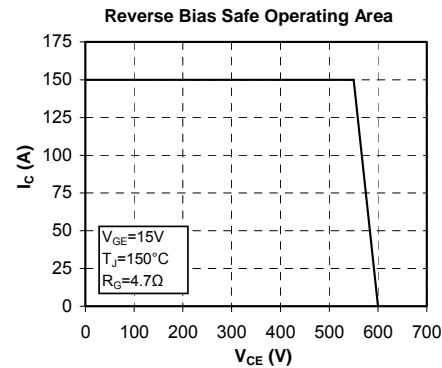
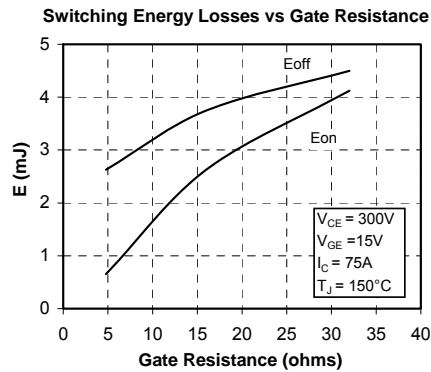
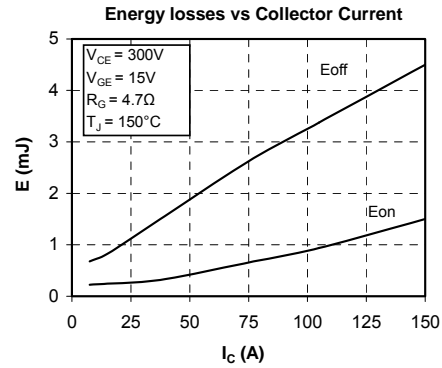
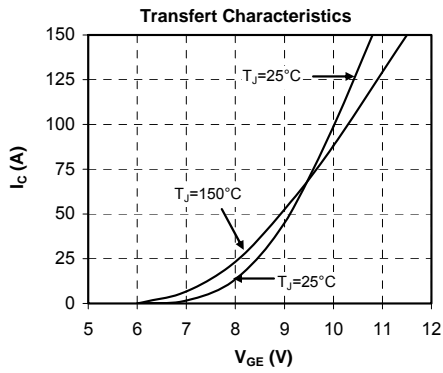
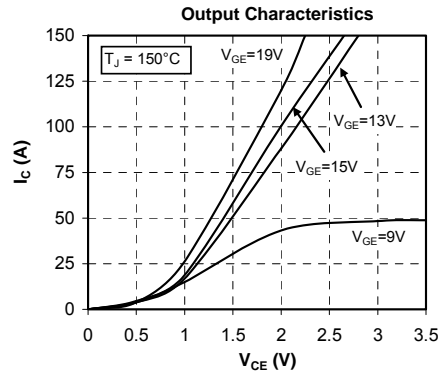
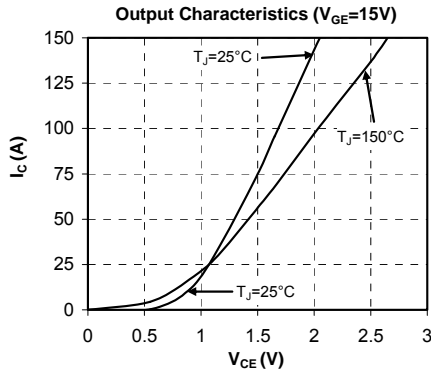
Symbol	Characteristic	Min	Typ	Max	Unit	
V_{ISOL}	RMS Isolation Voltage, any terminal to case $t=1$ min, $I_{isol}<1$ mA, 50/60Hz	2500			V	
T_J	Operating junction temperature range	-40		175*	°C	
T_{STG}	Storage Temperature Range	-40		125		
T_C	Operating Case Temperature	-40		100		
Torque	Mounting torque	To heatsink	M4	2.5	4.7	N.m
Wt	Package Weight				110	g

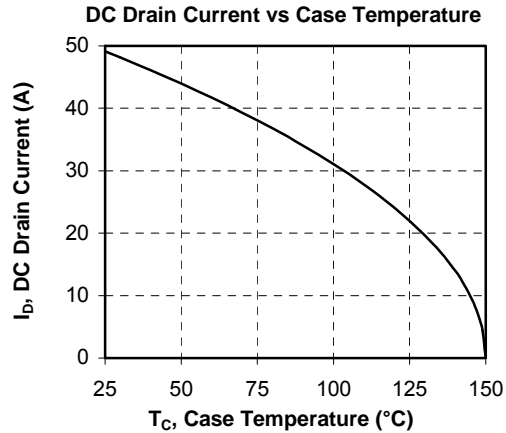
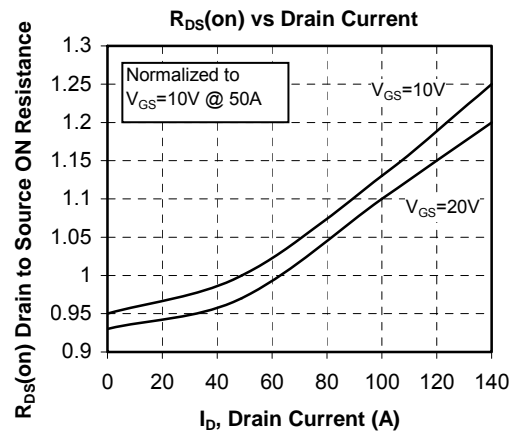
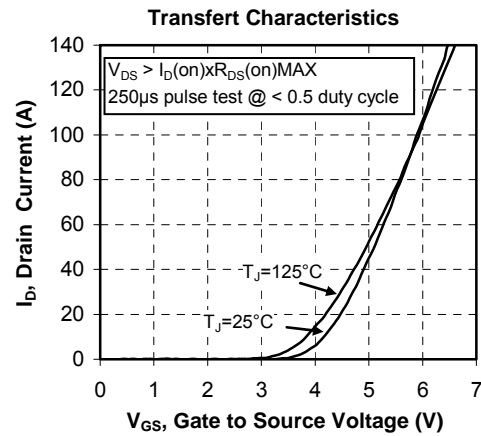
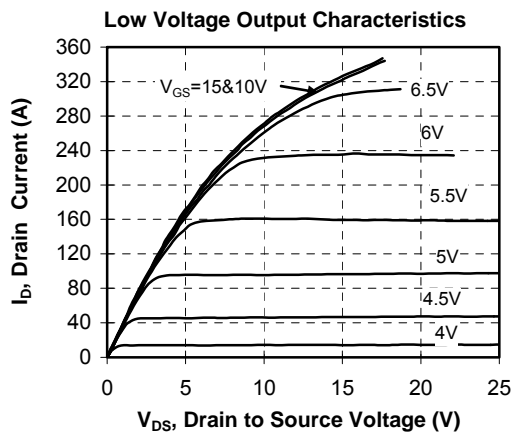
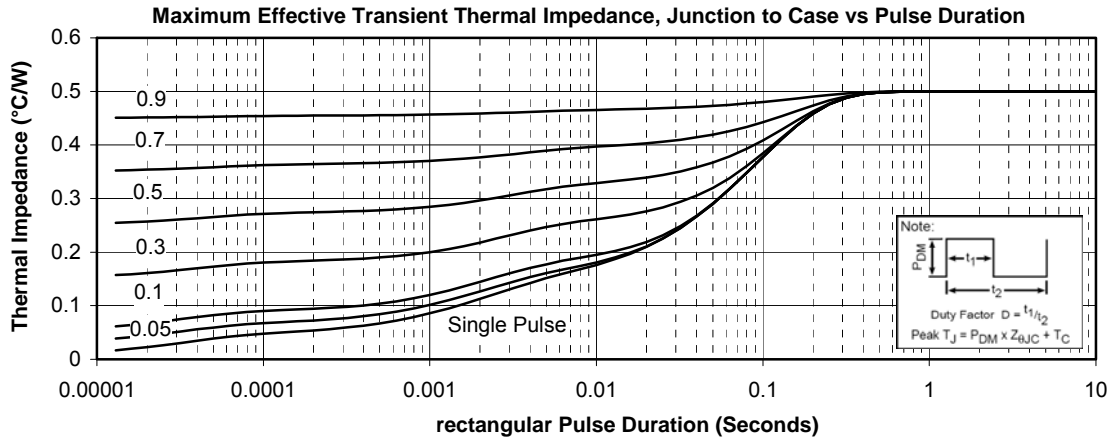
* $T_{jmax} = 150^{\circ}\text{C}$ for Q1 & Q4

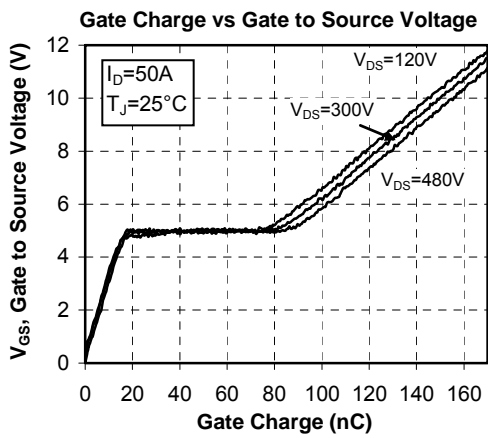
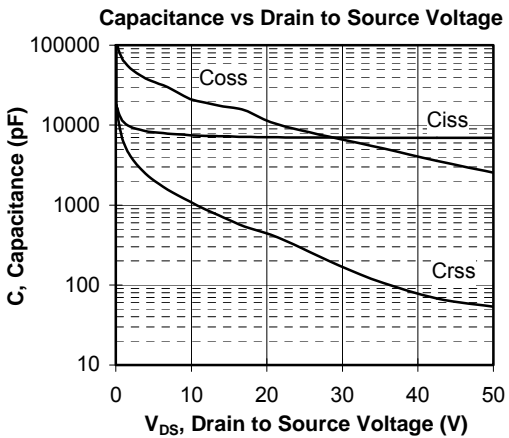
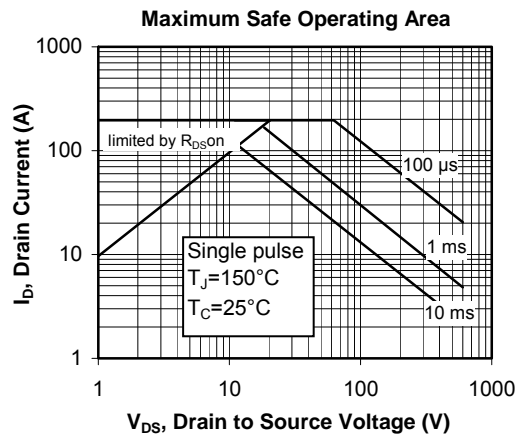
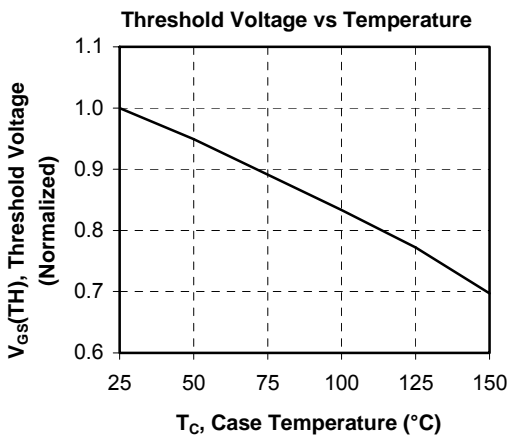
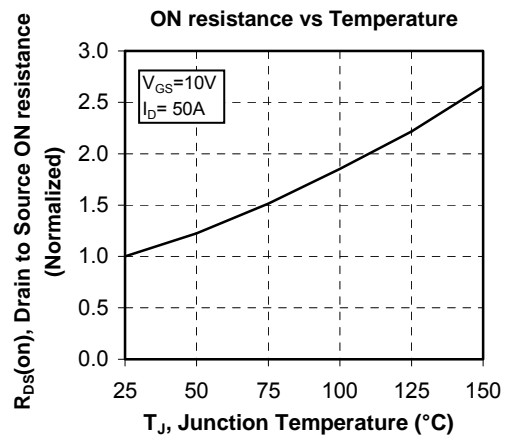
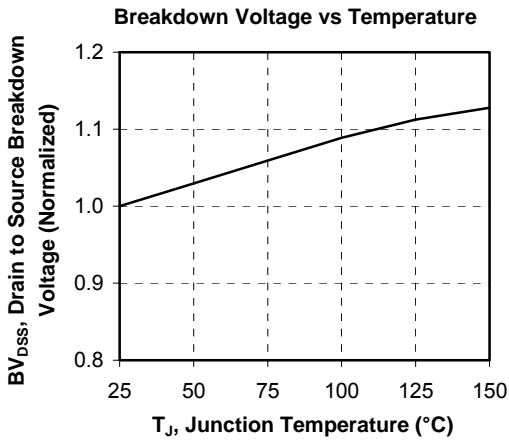
SP3 Package outline (dimensions in mm)


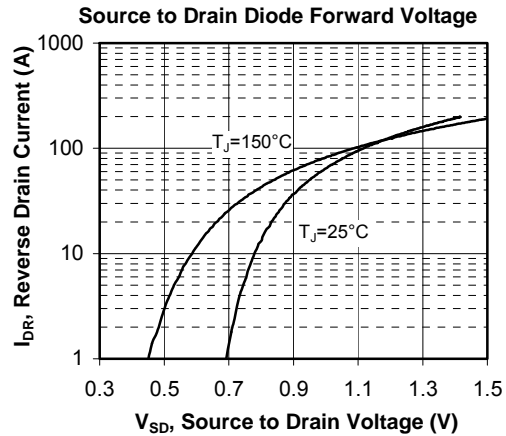
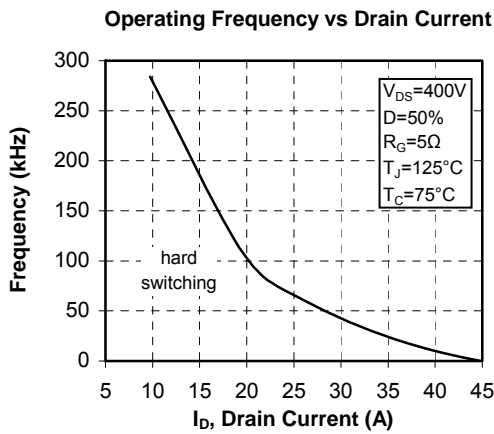
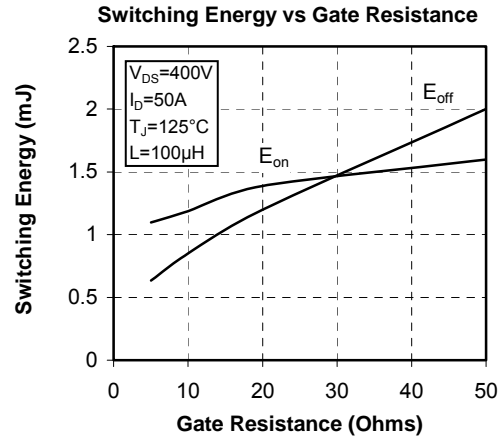
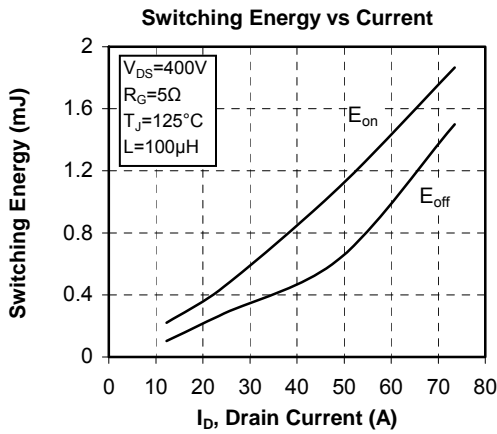
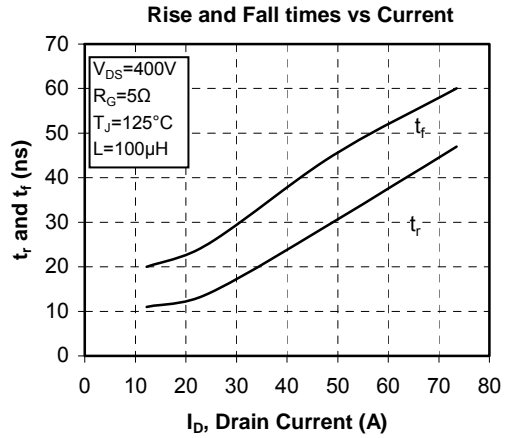
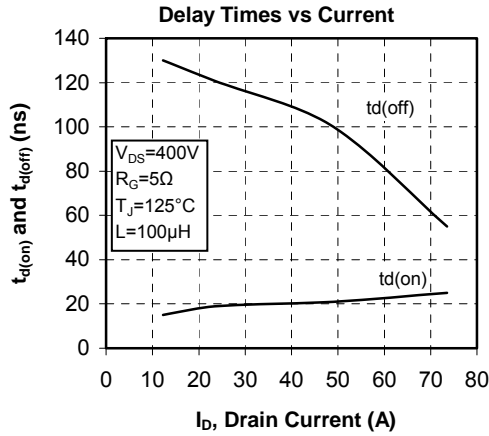
See application note 1901 - Mounting Instructions for SP3 Power Modules on www.microsemi.com

Q2 & Q3 Typical performance curve


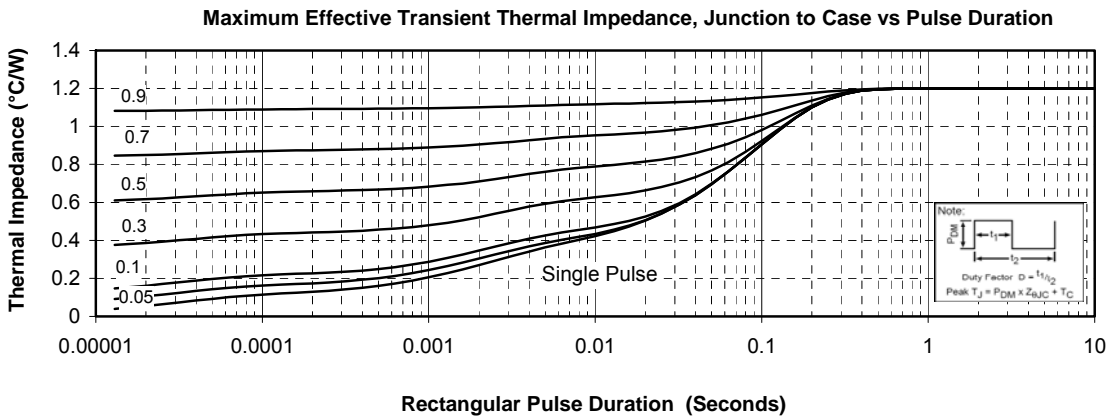
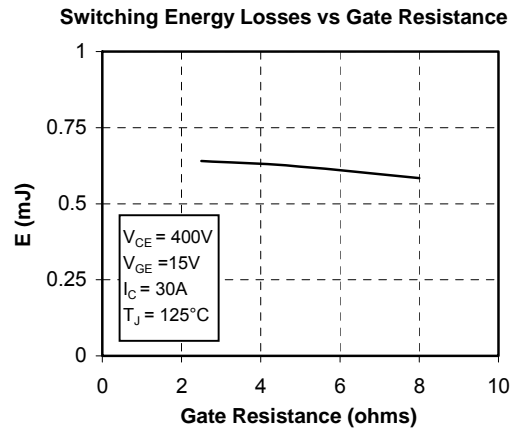
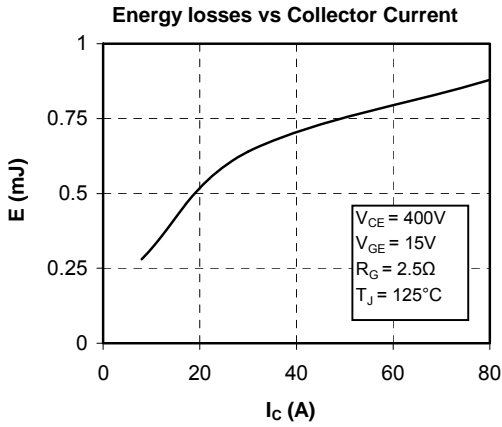
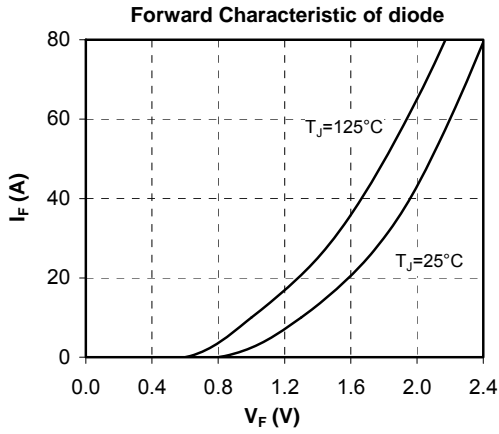


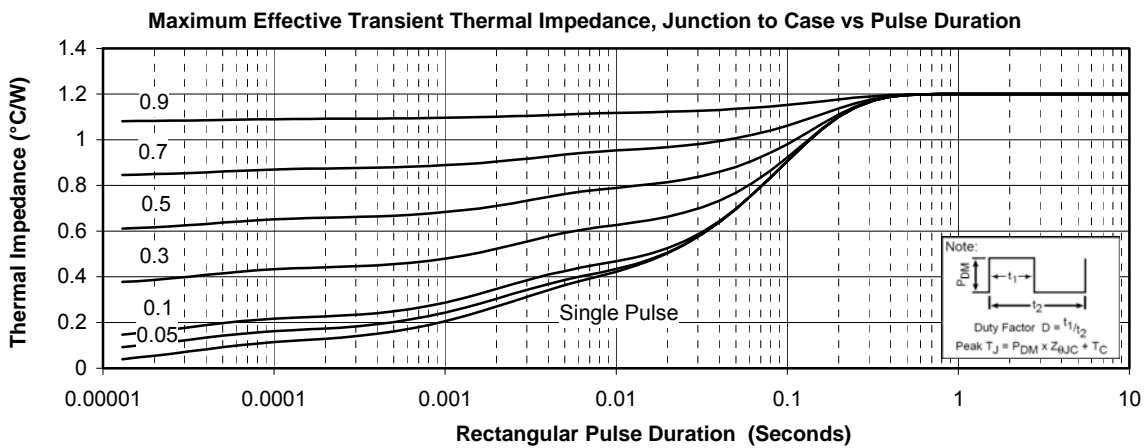
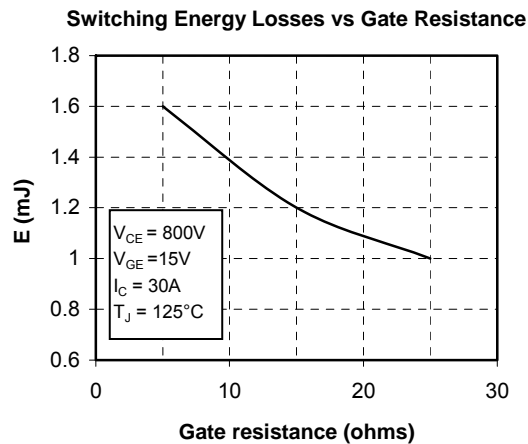
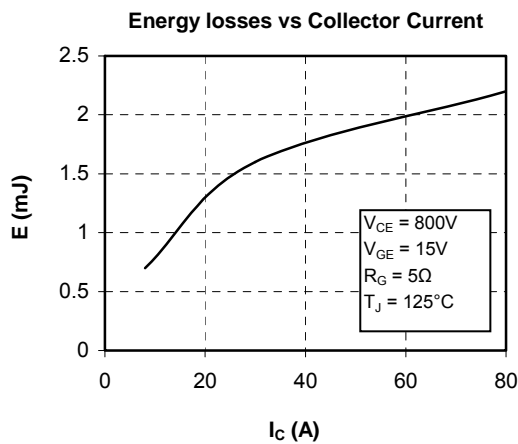
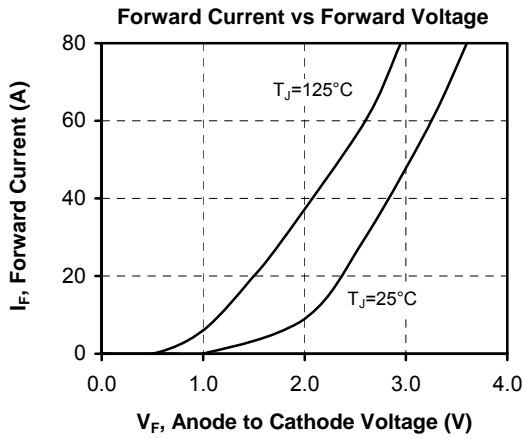
Q1 & Q4 Typical performance curve






CR5 & CR6 Typical performance curve



CR2, CR3, CR7 & CR8 Typical performance curve


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